

# PHOTOCOUPLER PS8701

# HIGH NOISE REDUCTION HIGH-SPEED ANALOG OUTPUT TYPE 5-PIN SOP PHOTOCOUPLER

#### **DESCRIPTION**

The PS8701 is an optically coupled isolator containing a GaAlAs LED on the light emitting diode (input side) and a PIN photodiode and a high-speed amplifier transistor on the output side on one chip.

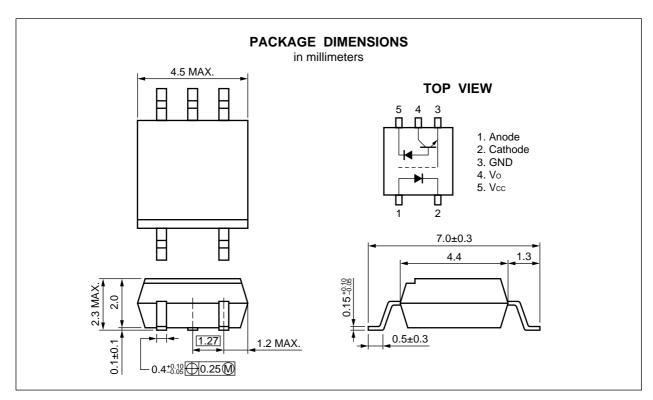
This is a plastic SOP (Small Out-line Package) type for high density applications.

#### **FEATURES**

- High common mode transient immunity (CMH, CML =  $\pm 10 \text{ kV/}\mu\text{s MIN.}$ )
- High supply voltage (Vcc = 35 V)
- High isolation voltage (BV = 2 500 Vr.m.s.)
- High-speed response (tphL = 0.8  $\mu$ s MAX., tpLH = 1.2  $\mu$ s MAX.)
- Taping product number (PS8701-E3, E4, F3, F4)

#### **APPLICATIONS**

- · Computer and peripheral manufactures
- · General purpose inverter
- Substitutions for relays and pulse transformers
- · Power supply



The information in this document is subject to change without notice.



### ABSOLUTE MAXIMUM RATINGS (TA = 25 °C, unless otherwise specified)

| Parameter                      |                   | Symbol           | Ratings     | Unit    |  |
|--------------------------------|-------------------|------------------|-------------|---------|--|
| Diode                          | Forward Current   | lF               | 25          | mA      |  |
|                                | Reverse Voltage   | VR               | 3.0         | V       |  |
|                                | Power Dissipation | Po               | 45          | mW      |  |
| Detector                       | Supply Voltage    | Vcc              | 35          | V       |  |
|                                | Output Voltage    | Vo               | 35          | ٧       |  |
|                                | Output Current    | lo               | 8.0         | mA      |  |
|                                | Power Dissipation | Pc               | 100         | mW      |  |
| Isolation Voltage <sup>1</sup> |                   | BV               | 2 500       | Vr.m.s. |  |
| Operating Ambient Temperature  |                   | TA               | -55 to +100 | °C      |  |
| Storage Temperature            |                   | T <sub>stg</sub> | -55 to +125 | °C      |  |

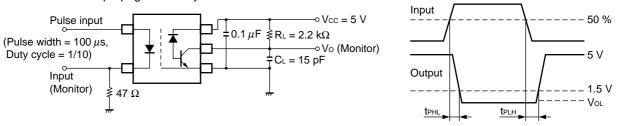
<sup>\*1</sup> AC voltage for 1 minute at T<sub>A</sub> = 25 °C, RH = 60 % between input and output

#### **ELECTRICAL CHARACTERISTICS (TA = 25 °C)**

| Parameter |  | Symbol                | Conditions  | MIN.             | TYP. | MAX. | Unit  |
|-----------|--|-----------------------|---|------------------|------|------|-------|
| Diode     | Forward Voltage  | VF                    | IF = 16 mA  |                  | 1.7  | 2.2  | V     |
|           | Reverse Current  | lr                    | VR = 3 V  |                  |      | 10   | μΑ    |
|           | Forward Voltage<br>Temperature Coefficient                             | $\Delta V_F/\Delta T$ | IF = 16 mA  |                  | -1.6 |      | mV/°C |
|           | Terminal Capacitance   | Ct                    | V = 0 V, f = 1 MHz  |                  | 60   |      | pF    |
| Detector  | High Level Output Current  | Іон (1)               | $I_F = 0 \text{ mA}, V_{CC} = V_0 = 5.5 \text{ V}$  |                  | 3    | 500  | nA    |
|           | High Level Output Current  | Іон (2)               | IF = 0 mA, Vcc = Vo = 30 V  |                  |      | 100  | μΑ    |
|           | Low Level Output Voltage   | Vol                   | IF = 16 mA, Vcc = 4.5 V, Io = 1.2 mA  |                  | 0.1  | 0.4  | V     |
|           | Low Level Supply Current   | ICCL                  | IF = 16 mA, Vo = open, Vcc = 30 V   |                  | 50   |      | μΑ    |
|           | High Level Supply Current  | Іссн                  | IF = 0 mA, Vo = open, Vcc = 30 V  |                  | 0.01 | 2    |       |
| Coupled   | Current Transfer Ratio   | CTR                   | IF = 16 mA, Vcc = 4.5 V, Vo = 0.4 V   | 15               | 20   | 35   | %     |
|           | Isolation Resistance   | R <sub>I-O</sub>      | V <sub>I-O</sub> = 1 kV <sub>DC</sub> , RH = 40 to 60 %   | 10 <sup>11</sup> |      |      | Ω     |
|           | Isolation Capacitance  | C <sub>I-O</sub>      | V = 0 V, f = 1 MHz  |                  | 0.4  |      | pF    |
|           | Propagation Delay Time $(H \rightarrow L)^{'1}$                        | <b>t</b> PHL          | $I_F = 16 \text{ mA}, \text{ Vcc} = 5 \text{ V}, \text{ RL} = 2.2 \text{ k}\Omega, \\ C_L = 15 \text{ pF}$        |                  | 0.5  | 0.8  | μs    |
|           | Propagation Delay Time (L → H) <sup>*1</sup>                           | <b>t</b> PLH          |   |                  | 0.6  | 1.2  |       |
|           | Common Mode<br>Transient Immunity at<br>High Level Output <sup>2</sup> | Смн                   | $I_F = 0 \text{ mA, } V_{CC} = 5 \text{ V, } R_L = 4.1 \text{ k}\Omega,$ $V_{CM} = 1.5 \text{ kV}$                | 10               |      |      | kV/μs |
|           | Common Mode<br>Transient Immunity at<br>Low Level Output <sup>2</sup>  | Смь                   | $I_F = 16 \text{ mA}, \text{ Vcc} = 5 \text{ V}, \text{ RL} = 4.1 \text{ k}\Omega,$ $\text{VcM} = 1.5 \text{ kV}$ | -10              |      |      |       |

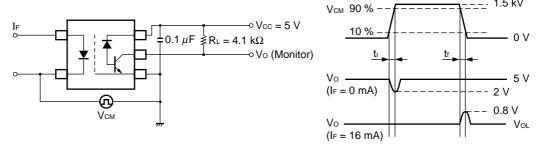


\*1 Test circuit for propagation delay time



C<sub>L</sub> is approximately 15 pF which includes probe and stray wiring capacitance

\*2 Test circuit for common mode transient immunity

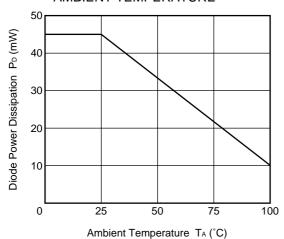


#### **USAGE CAUTIONS**

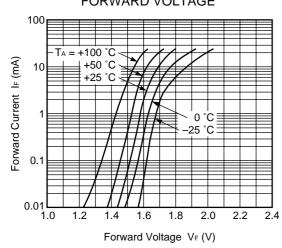
- 1. This product is weak for static electricity by designed with high-speed integrated circuit so protect against static electricity when handling.
- 2. By-pase capacitor of more than 0.1  $\mu F$  is used between Vcc and GND near device.

#### TYPICAL CHARACTERISTICS (TA = 25 °C, unless otherwise specified)

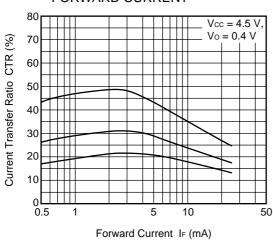
## DIODE POWER DISSIPATION vs. AMBIENT TEMPERATURE



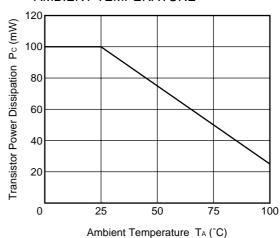
## FORWARD CURRENT vs. FORWARD VOLTAGE



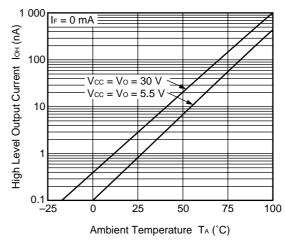
## CURRENT TRANSFER RATIO vs. FORWARD CURRENT



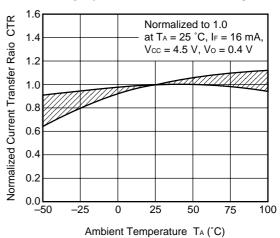
### TRANSISTOR POWER DISSIPATION vs. AMBIENT TEMPERATURE



# HIGH LEVEL OUTPUT CURRENT vs. AMBIENT TEMPERATURE

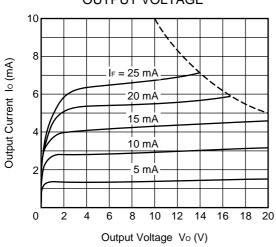


## NORMALIZED CURRENT TRANSFER RATIO vs. AMBIENT TEMPERATURE

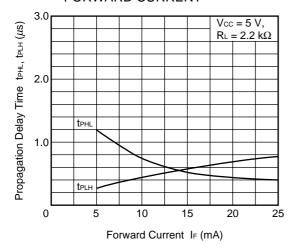


### **NEC**

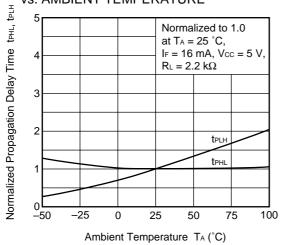
## OUTPUT CURRENT vs. OUTPUT VOLTAGE



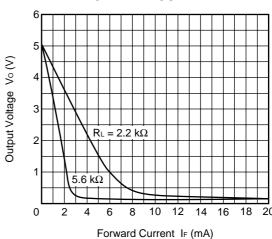
## PROPAGATION DELAY TIME vs. FORWARD CURRENT



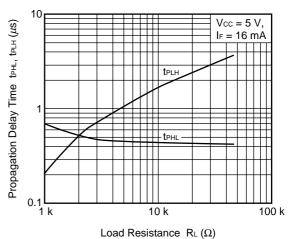
# NORMALIZED PROPAGATION DELAY TIME vs. AMBIENT TEMPERATURE



## OUTPUT VOLTAGE vs. FORWARD CURRENT

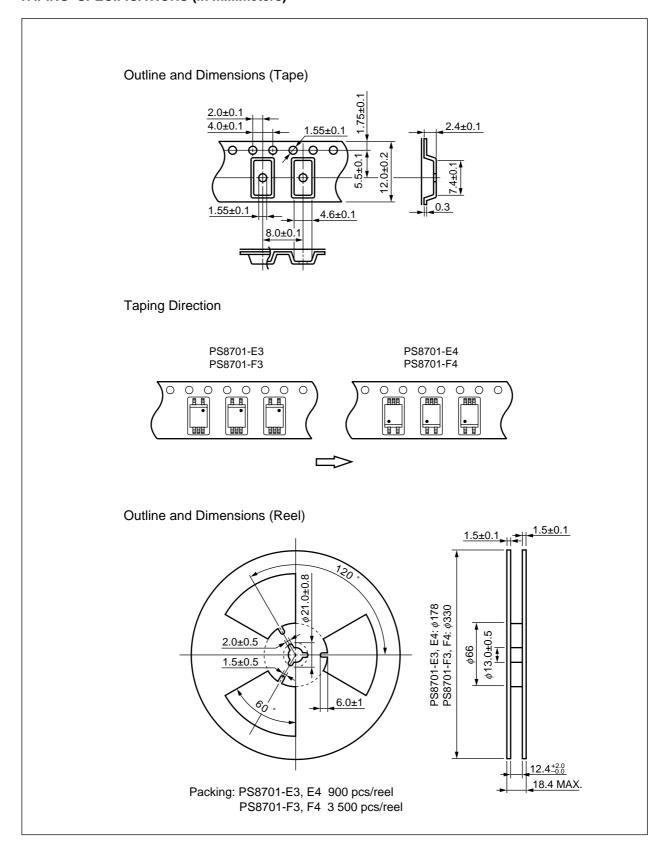


## PROPAGATION DELAY TIME vs. LOAD RESISTANCE





#### **TAPING SPECIFICATIONS (in millimeters)**





#### RECOMMENDED SOLDERING CONDITIONS

#### (1) Infrared reflow soldering

• Peak reflow temperature 235 °C (package surface temperature)

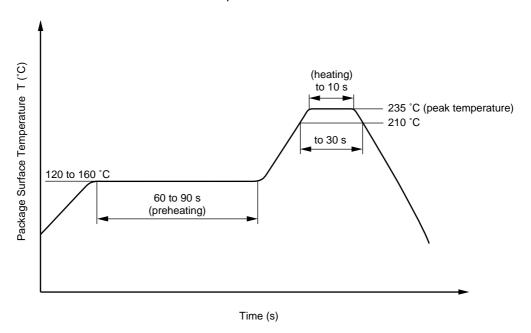
• Time of temperature higher than 210 °C 30 seconds or less

• Number of reflows Three

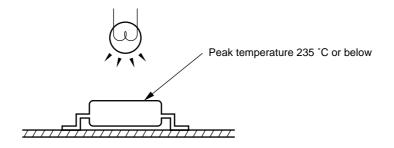
Flux
Rosin flux containing small amount of chlorine (The flux with a

maximum chlorine content of 0.2 Wt % is recommended.)

#### Recommended Temperature Profile of Infrared Reflow



Caution Please avoid to removed the residual flux by water after the first reflow processes.



#### (2) Dip soldering

• Temperature 260 °C or below (molten solder temperature)

• Time 10 seconds or less

• Number of times One

• Flux Rosin flux containing small amount of chlorine (The flux with a maximum chlorine content of

0.2 Wt % is recommended.)

#### **CAUTION**

Within this device there exists GaAs (Gallium Arsenide) material which is a harmful substance if ingested. Please do not under any circumstances break the hermetic seal.

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Anti-radioactive design is not implemented in this product.

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